

**Amendments to the Claims:**

This listing of claims will replace all prior versions, and listings, of claims in the present application:

**Listing of Claims:**

Claim 1-13 (cancelled)

Claim 14 (original) A method of forming a common carrier comprising the steps of:  
adhering an unprocessed, integrateable form of a plurality of chips on the upper surface of a carrier substrate according to a first placement alignment precision;  
lithographically processing the unprocessed, integrateable form of the plurality of chips to form a plurality of integrated chips on the upper surface, wherein the integrated chips are aligned with each other and the substrate with a second alignment precision having lithographic processing tolerances.

Claim 15 (original) The method of forming the common carrier as described in Claim 14 wherein the first alignment precision has a greater tolerance range than the lithographic processing tolerances.

Claim 16 (original) The method of forming the common carrier as described in Claim 14 wherein the first alignment precision has a tolerance in the range of +/- 1 millimeter and the second alignment precision has a tolerance in the range of less than 1 micron.

Claim 17 (original) The method of forming the common carrier as described in Claim 14 further comprising the steps of:

forming a plurality of slots within the upper surface of the carrier substrate according to the first alignment precision; and

adhering the unprocessed, integrateable form of the integrated chips within the plurality of slots.

Claim 18 (original) The method of forming the common carrier as described in Claims 17 further comprising the step of depositing a filler so as to fill a peripheral gap between the interior edges of each of the slots and the peripheral edges of each of the unprocessed, integrateable form of the integrated chips when each unprocessed chip is adhered within each slot.

Claim 19 (original) The method of forming the common carrier as described in Claim 18 further comprising the step of polishing the upper surface of the plurality of chips to be in essentially the same parallel plane as the upper surface of the carrier substrate.

Claim 20 (original) The method of forming the common carrier as described in Claim 14 further comprising the step of adhering the unprocessed, integrateable form of the integrated chips directly on the upper surface of the carrier substrate such that the upper surface of the unprocessed, integrateable chips is in a parallel, but different, plane than the upper surface of

the substrate carrier.

Claim 21 (original) The method of forming the common carrier as described in Claim 20 further comprising the step of lithographically processing using curtain coating deposition.